

General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

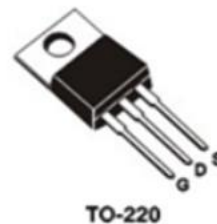
Features

cell density Trench technology
 $R_{DS(ON)}$ to minimize conductive loss

Application

nd Synchronous Rectifier

Product Summary



Ordering Information:

	TUBE
	800

Absolute Maximum Ratings $T_C=25$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D @ T_C=25$	110	A
	$I_D @ T_C=75$	84	A
	$I_D @ T_C=100$	69	A
Pulsed Drain Current	I_{DM}	330	A
Total Power Dissipation	$P_D @ T_C=25$	69	W
Total Power Dissipation	$P_D @ T_A=25$	2.7	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	80	mJ

Fig.7 Gate Charge Characteristics

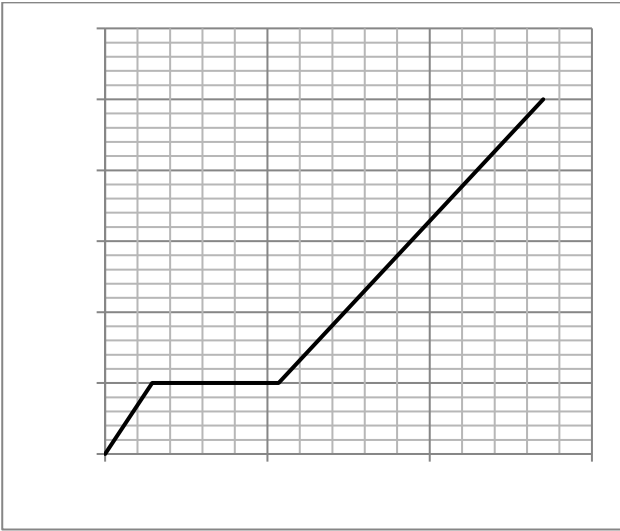


Fig.8 Capacitance vs Vds

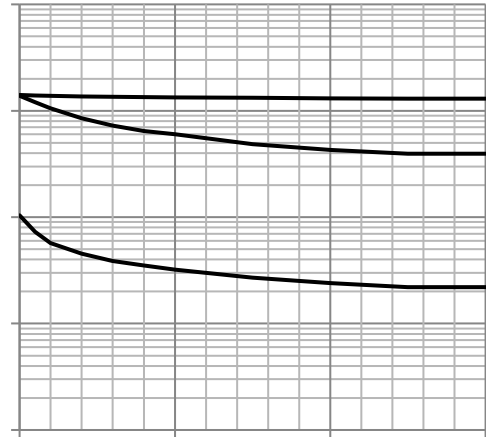


Fig.9 SOA Maximum Safe Operating Area

Fig.10 ID-Junction Temperature

Fig.11 Switching Time Measurement Circuit

Fig.12 Gate Charge Waveform

Fig.13 Resistive Switching Test Circuit

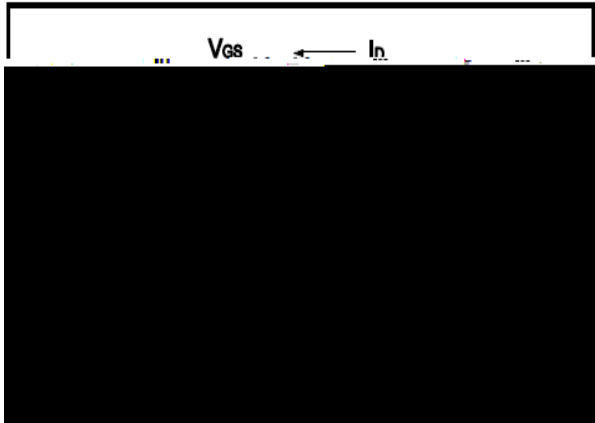


Fig.14 Resistive Switching Test Waveform

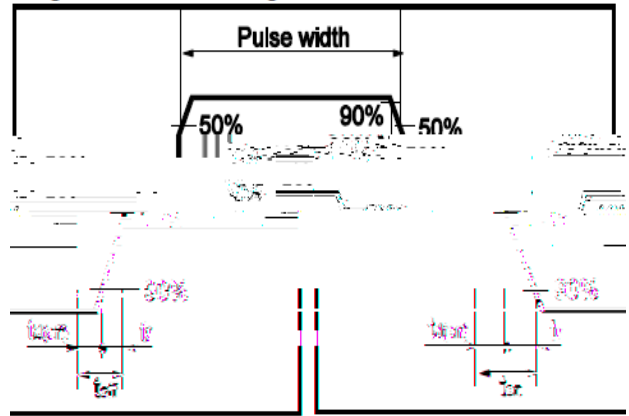


Fig.15 Avalanche Measurement Circuit

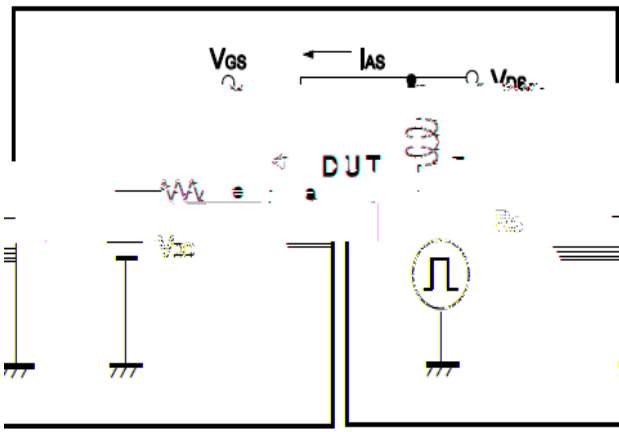


Fig.16 Avalanche Waveform

